



•

•

.

•

•

•

•

•

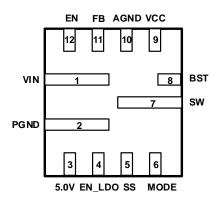
•

•

1)	

Over operating free-air temperature unless otherwise noted⁽¹⁾

DESCRIPTION	MIN	MAX	UNIT
VIN, EN	-0.3	32	V
SW	-1	32	V
BST	-0.3	38	V
BST-SW	-0.3	6	V
VOUT	-0.3	16	V
5.0V, EN_LDO, MODE, VCC, FB	-0.3	6	V
Operating junction temperature ⁽²⁾	-40	125	С
Storage temperature T _{STG}	-65	150	С



Top View: QFN-12L 3mm x 3mm, Plastic

(1)

(2)

VIN	1	Input voltage. Decouple the input rail with at least a 0.1uF and 10uF input ceramic capacitor. Place the capacitor as close to VIN and PGND pins as possible. Use wide PCB traces and multiple vias to make the connection.
PGND	2	Power ground. Using wide PCB traces and multiple vias large enough to handle the load current.
5.0V	3	The output of the 5.0V, 150mA LDO output, at least a 4.7uF ceramic cap connected between VCC pin and ground.
EN LDO		

EN_LDO 4



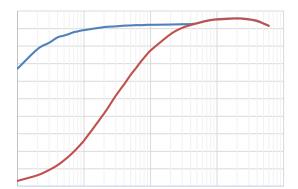
SW	7	Switch output. SW is driven up to VIN through the high-side power MOSFET during on-time. The inductor current drives SW to negative voltage through low-side power MOSFET during off-time. Use wide and short PCB traces to make the connection. Keep the SW pattern area minimized.
BST	8	Bootstrap. Must connect a 0.1uF capacitor or greater between SW and BST to form a floating supply across the gate driver of high-side power MOSFET.
VCC	9	Internal VCC LDO output. The driver and control circuits are powered by VCC. Decouple with 1µF ceramic capacitor placed as close to VCC as possible.
AGND	10	



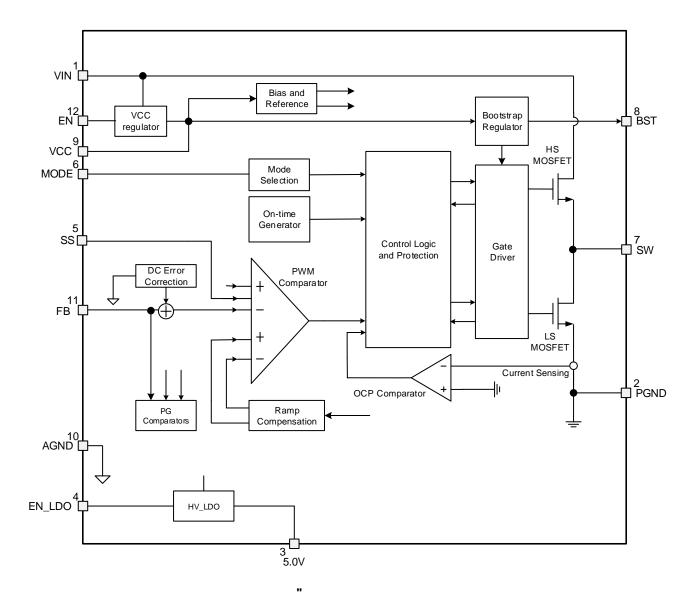
				<u> </u>	
		I			
			T		
				<u> </u>	
-					
_					
			•		
		-	•	•	















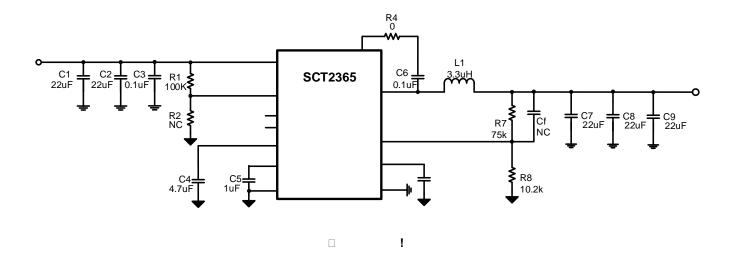


<u> </u>		
	 '	
_		
•		









Design Parameters	Example Value
Input Voltage	12V
Output Voltage	5V
Output Current	6A
Output voltage ripple (peak to peak)	50mV
Switching Frequency	400kHz

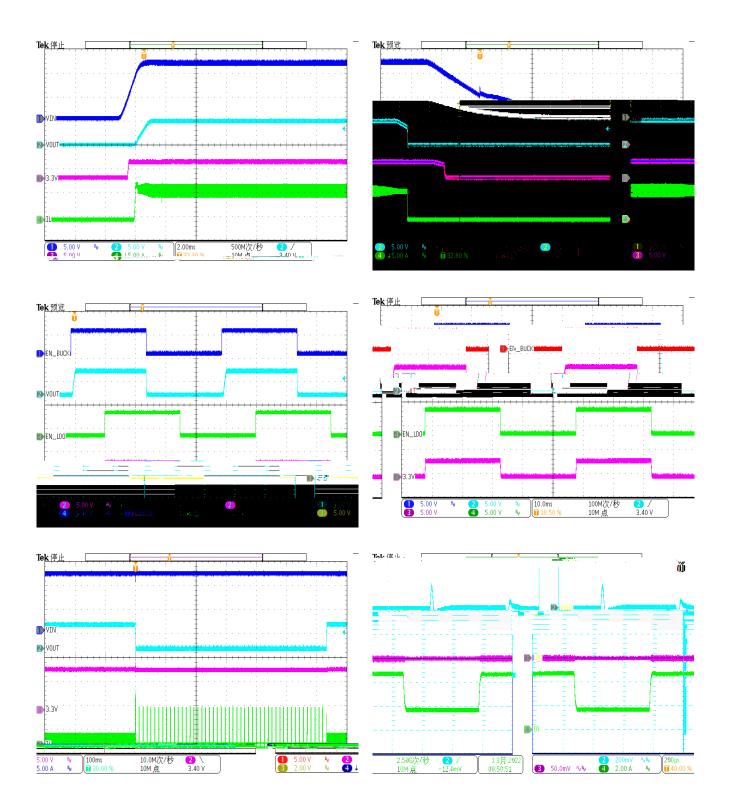


*

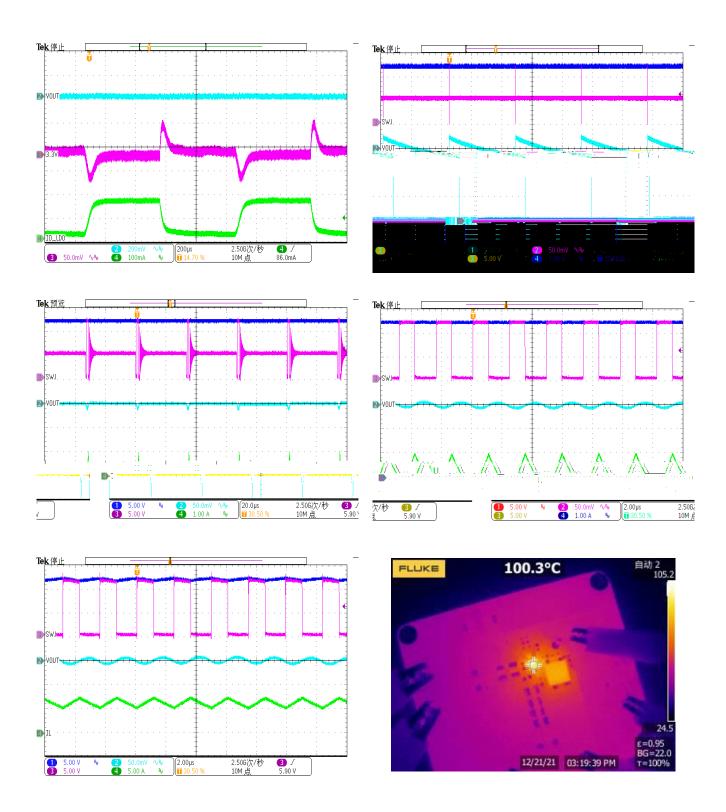
•













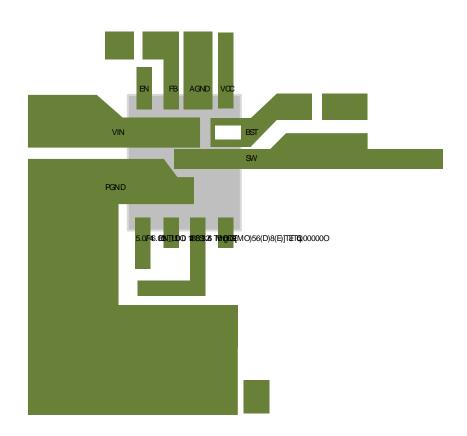
2.

3.

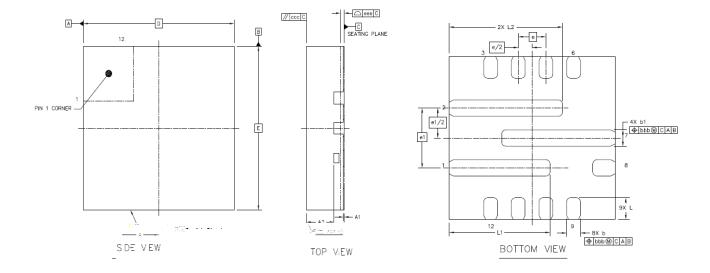
4.

5.

6.



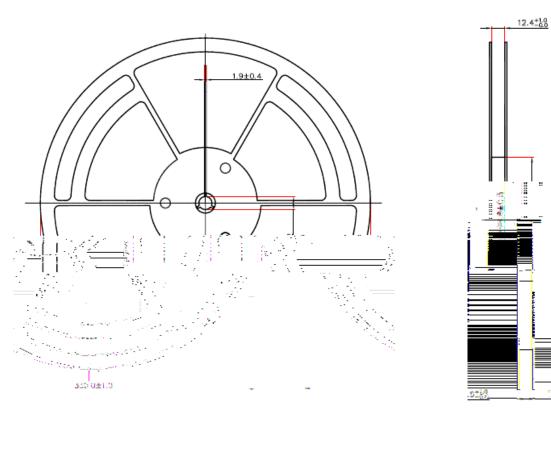


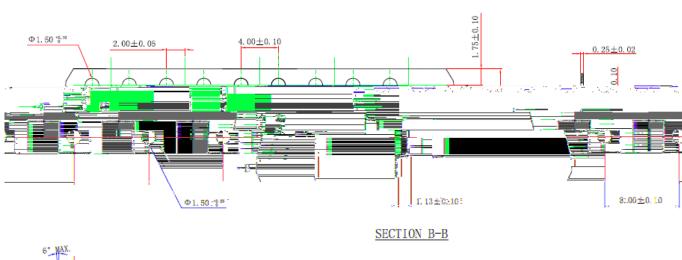


	_	
	_	

1. 2. 3. 4. 5.







SECTION A-A

